International TOR Rectifier

HFA25TB60

HEXFRED™

Ultrafast, Soft Recovery Diode

Features

- Ultrafast Recovery
- Ultrasoft Recovery
- Very Low I_{RRM}
- · Very Low Qrr
- · Specified at Operating Conditions

Benefits

- · Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- · Higher Frequency Operation
- · Reduced Snubbing
- · Reduced Parts Count



Description

International Rectifier's HFA25TB60 is a state of the art ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 volts and 25 amps continuous current, the HFA25TB60 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA25TB60 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.



Absolute Maximum Ratings

	Parameter	Max	Units	
V _R	Cathode-to-Anode Voltage	600	V	
I _F @ T _C = 100°C	Continuous Forward Current	25		
I _{FSM}	Single Pulse Forward Current	225	Α	
I _{FRM}	Maximum Repetitive Forward Current	100		
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	125	С	
P _D @ T _C = 100°C	Maximum Power Dissipation	50]	
TJ	Operating Junction and	-55 to +150	w	
T _{STG}	Storage Temperature Range	-55 (0 +150	VV	

^{* 125°}C

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	U V	• ,						
	Parameter	Min	Тур	Max	Units	Test Conditions		
V _{BR}	Cathode Anode Breakdown Voltage	600			V	I _R = 100μA		
V _{FM}	Max Forward Voltage		1.3	1.7	V	I _F = 25A		
			1.5	2.0		I _F = 50A	See Fig. 1	
			1.3	1.7		I _F = 25A, T _J = 125°C		
I _{RM}	Max Reverse Leakage Current		1.5	20	μA	V _R = V _R Rated	See Fig. 2	
			600	2000		$T_J = 125^{\circ}C$, $V_R = 0.8 \times V_R$ Rated		
C _T	Junction Capacitance		55	100	pF	V _R = 200V	See Fig. 3	
LS	Series Inductance		8.0	.0	nH	Measured lead to lead	5mm from	
			0.0		ш	package body		

Dynamic Recovery Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min	Тур	Max	Units	Test Conditions		
t _{rr}	Reverse Recovery Time		23			$I_F = 1.0A$, $di_f/dt = 200A/\mu s$, $V_R = 30V$		
t _{rr1}	See Fig. 5, 6 & 16		50	75	ns	T _J = 25°C		
t _{rr2}	•		105	160		T _J = 125°C	I _F = 25A	
I _{RRM1}	Peak Recovery Current		4.5	10	Α	T _J = 25°C		
I _{RRM2}	See Fig. 7& 8		8.0	15	_ ^	T _J = 125°C	V _R = 200V	
Q _{rr1}	Reverse Recovery Charge		112	375	nC	T _J = 25°C	1	
Q _{rr2}	See Fig. 9 & 10		420	1200	IIC	T _J = 125°C	di _f /dt = 200A/µs	
di _{(rec)M} /dt1	Peak Rate of Fall of Recovery Current		250		A/µs	T _J = 25°C]	
di _{(rec)M} /dt2	During t _b See Fig. 11 & 12		160		Α/μS	T _J = 125°C		

Thermal - Mechanical Characteristics

	Parameter	Min	Тур	Max	Units
T _{lead} ①	Lead Temperature			300	°C
RthJC	Thermal Resistance, Junction to Case			1.0	
R _{thJA} @	Thermal Resistance, Junction to Ambient			80	K/W
R _{thCS} ®	Thermal Resistance, Case to Heat Sink		0.5		
Wt	Weight		2.0		g
	Weight		0.07		(oz)
	Mounting Torque	6.0		12	Kg-cm
······································	Wisding Forque	5.0		10	lbf•in

 $^{\, \}oplus \,$ 0.063 in. from Case (1.6mm) for 10 sec

② Typical Socket Mount

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Mounting Surface, Flat, Smooth and Greased

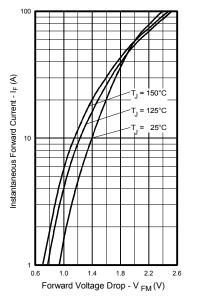


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

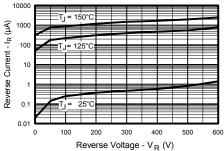


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

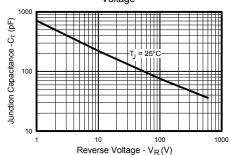


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

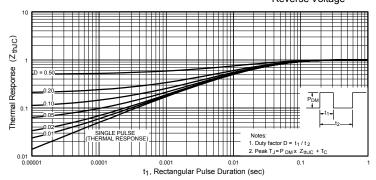
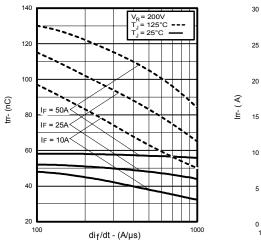


Fig. 4 - Maximum Thermal Impedance Z_{thjc} Characteristics

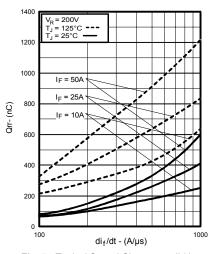
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 $\begin{array}{c} 30 \\ \hline V_R = 200V \\ \hline T_J = 125^{\circ}C \\ \hline 25 \\ \hline \end{array}$

Fig. 5 - Typical Reverse Recovery vs. di_f/dt

Fig. 6 - Typical Recovery Current vs. di_f/dt



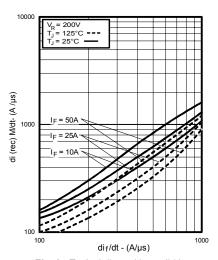


Fig. 7 - Typical Stored Charge vs. di_f/dt

Fig. 8 - Typical di_{(rec)M}/dt vs. di_f/dt

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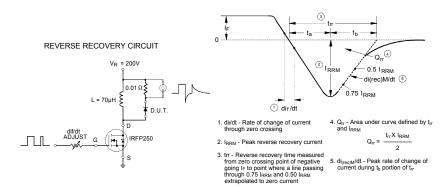
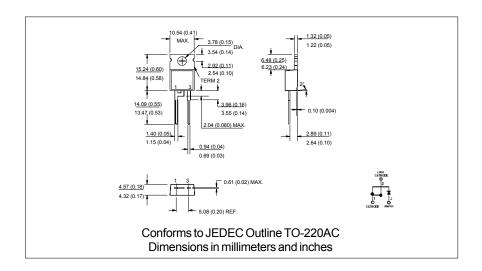


Fig. 9 - Reverse Recovery Parameter Test Circuit

Fig. 10 - Reverse Recovery Waveform and Definitions

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